

# **Nanosecond SCR SWITCH**

**PRODUCT PREVIEW** 

### **DESCRIPTION**

Designed for high current narrow-pulse switching applications where size and current handling capability are critical. These devices may be triggered on using low power logic drivers from (+0.8 V at 200  $\mu$ A).

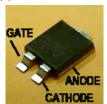
Epoxy packaged, oxide passivated planar SCR chips with metallurgic bonds on both sides to achieve high reliability. Internal wire bond connection allows high current surge capability for narrow pulse applications.

IMPORTANT: For the most current data, consult MICROSEM? swebsite: http://www.microsemi.com

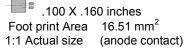
#### **ABSOLUTE MAXIMUM RATINGS AT 25° C** (UNLESS OTHERWISE SPECIFIED) Rating Symbol Value Unit Repetative peak Off-State Voltage $V_{DRM}$ 60 V Peak On-State Current $I_{\text{TSM}}$ 100 Α Peak Gate Current 250 $I_{\mathsf{GM}}$ mΑ $V_{\mathsf{GR}}$ 5 V Reverse Gate Current Storage Temperature Range Τs -50 to 150 °C ТJ -25 to 125 ٥С Operating Temperature Range

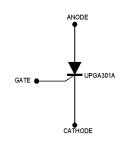
THERMAL CHARACTERISTICS (UNLESS OTHERWISE SPECIFIED)					
Thermal Resistance	_				
Junction-to Case (Anode)	RJ	4.0	°C/Watt		

- (1) Mounted on 2" square by 0.06' thick FR4 board with a 1" x 1" square 2 ounce copper pattern.
- (2) Mounted on 0.06 thick FR4 board, using recommended footprint.



Small foot print





### **KEY FEATURES**

- Powermite 3 ® Package
- Small Mechanical Outline
- High speed switching capability
- Logic drive capability (0.8V, 200μA)
- UIS Rated Available with Lot Acceptance Testing
- Ideal for Laser Range finder and Camera Applications
- Ideal for Automotive Collision Avoidance Applications
- Available in 16mm Tape and Reel—6000 units/reel

### **APPLICATIONS/BENEFITS**

Microsemi Corp DN14 design note

Nanosecond SCR switch for reliable high current pulse generators, modulators and photo-flash quenching.

Several new applications for nanosecond SCR switches include automotive collision avoidance systems, laser drivers, photo-flash quenching circuits, specially developed circuits for the emerging digital imaging range finders and communication markets.



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ELECTRICAL PARAMETERS@25°C (unless otherwise specified)								
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units		
▶ On characteristics (up to 100 A w/ 100 ns pulse @ Duty Cycle = 0.0001% or less)								
Forward Blocking Current	$I_{DRM}$	$V_{DRM} = 50V$ , $R_{GK} = 1k \Omega$			100	nA		
On - State Voltage	V <sub>T</sub>	$I_T = 1A$ , $Ig = 10mA$		1.1	1.5	V		
Gate Trigger Voltage	$ m V_{GT}$	$V_{\rm D} = 5V, R_{\rm GS} = 100\Omega$		0.5	0.75	V		
Gate Trigger Current	I <sub>GT</sub>	$V_D = 5V$ , $R_{GS} = 10k\Omega$		2	20	μΑ		
Reverse Gate Current	$I_{GR}$	$V_{GR}$ = 5V		0.01	0.1	mA		
Holding Current	$I_{\mathrm{H}}$	$V_D = 5V$ , $R_{GK} = 1k\Omega$	0.3	1.0	2.5	mA		
Reverse Current (note 1)	$I_{RRM}$	$V_{RRM}$ = 30V, $R_{GK}$ = 1k $\Omega$		1	10	mA		
► Switching characteristics (Tc = 25 °C)								
Delay Time	Td	$Ig = 20 \text{ mA}, I_T = 1A$		20	30	ns		
Rise Time	tr	$V_D = 50V$ , $I_T = 1A$ , $Ig = 10mA$ DC < 1%		15	25	ns		
Circuit Commutated Turn—off Time	tq	$I_T = I_R = 1A$ , $R_{GK} = 1k\Omega$		0.3	0.5	μs		
Gate Trigger—on Pulse Width	tpg(on)	$Ig = 10mA, I_T = 1A$		20	50	ns		
Critical Rate of Rise Off –State Voltage	dv/dt	$V_D$ = 30V, $R_{GK}$ = 1k $\Omega$	15	30		V/μs		

Note 1: Pulse Test intended to guarantee reverse anode voltage capability for pulse commutation.

### SPICE MODEL

.subckt SCR anode gate cathode PARAMS:

\* Powermite 3 UPGA350A high-speed thyristor

+Vdrm= 60V Vrrm=30V Idrm=1μA Ih=5mA +dvdt=7E5V/s Igt=200μA Vgt=.75V Vtm=1.5V

+Itm=2A ton=55ns toff=500ns

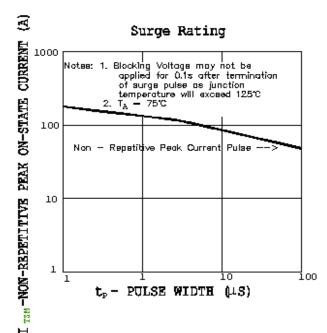
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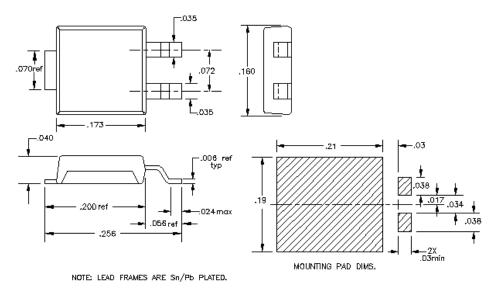


# Switching Speed vs. Current 1000 Rated Vorm Notes: 1. ٧6 E IG 2. 3. 4. = 25°C 9 t<sub>D</sub> = 200 mA t<sub>D</sub> = 20ns typ. Independent of anods current. -TYPICAL RISE TIME 100 10 1 100 -ANODE CURRENT (A)

Case: Molded Epoxy Meets UL94VO at 1/8 inch Weght: 72 milligrams

Lead and Mounting Temperature: 260°C max for 10 seconds

# NOTE: All dimensions are in inches.





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